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ON Semiconductor
NTGS1135PT1G

For any questions, you can email us directly:
sales@integrated-circuit.com

NTGS1135P

Power MOSFET

−8 V, −5.8 A, Single P−Channel, TSOP−6

Features

- Ultra Low $R_{DS(on)}$
- 1.2 V $R_{DS(on)}$ Rating
- This is a Pb−Free Device

Applications

- Load Switch
- Battery Management

ON Semiconductor®

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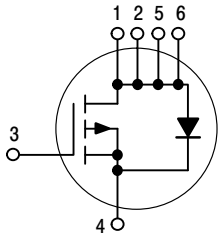
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
−8 V	31 mΩ @ −4.5 V	−4.6 A
	38 mΩ @ −2.5 V	
	57 mΩ @ −1.8 V	
	300 mΩ @ −1.2 V	

P−Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−8.0	V
Gate−to−Source Voltage			V_{GS}	±6.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−4.6	A
		T_A = 85°C		−3.3	
	t ≤ 5 s	T_A = 25°C		−5.8	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	0.97	W
	t ≤ 5 s			1.6	
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−9.2	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

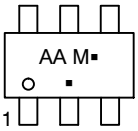
1. Surface−mounted on FR4 board using 1 in sq pad size (Cu area = 1 in sq [2 oz] including traces)
2. Surface−mounted on FR4 board using the minimum recommended pad size. (Cu area = 0.0751 in sq)

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	128	°C/W
Junction−to−Ambient − t = 5 s (Note 1)	$R_{\theta JA}$	78	
Junction−to−Ambient − Steady State (Note 2)	$R_{\theta JA}$	188	

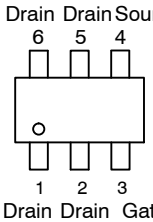
TSOP−6
CASE 318G
STYLE 1

MARKING DIAGRAM



AA = Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
NTGS1135PT1G	TSOP−6 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA	−8.0			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = −250 μA, Ref to 25°C		−8.4		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −6 V			−1.0	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±6 V			±100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA	−0.35	−0.57	−0.85	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.8		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −4.6 A		22	31	mΩ
		V_{GS} = −2.5 V, I_D = −2.5 A		28	38	
		V_{GS} = −1.8 V, I_D = −2.0 A		37	57	
		V_{GS} = −1.5 V, I_D = −1.0 A		47	73	
		V_{GS} = −1.2 V, I_D = −0.1 A		100	300	
Forward Transconductance	g_{FS}	V_{DS} = −4.0 V, I_D = −3.0 A		1.2		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = −6.0 V		2200		pF
Output Capacitance	C_{OSS}			400		
Reverse Transfer Capacitance	C_{RSS}			200		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −8.0 V; I_D = −2.5 A		21		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.9		
Gate−to−Source Charge	Q_{GS}			2.8		
Gate−to−Drain Charge	Q_{GD}			3.9		
SWITCHING CHARACTERISTICS (Note 4)						
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DS} = −8.0 V, I_D = −2.5 A, R_G = 6.2 Ω		10		ns
Rise Time	t_r			16		
Turn−Off Delay Time	$t_{d(OFF)}$			128		
Fall Time	t_f			71		
DRAIN−SOURCE DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.0 A, T_J = 25°C		−0.6	−1.0	V
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = −1.0 A		25		ns
Charge Time	t_a			11		
Discharge Time	t_b			14		
Reverse Recovery Charge	Q_{RR}			13		nC

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
4. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

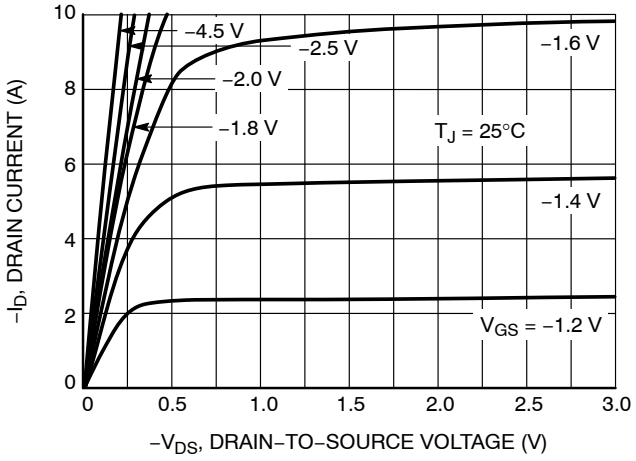


Figure 1. On−Region Characteristics

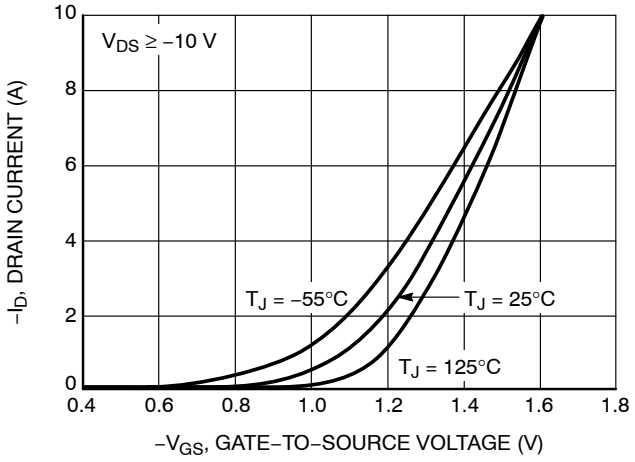


Figure 2. Transfer Characteristics

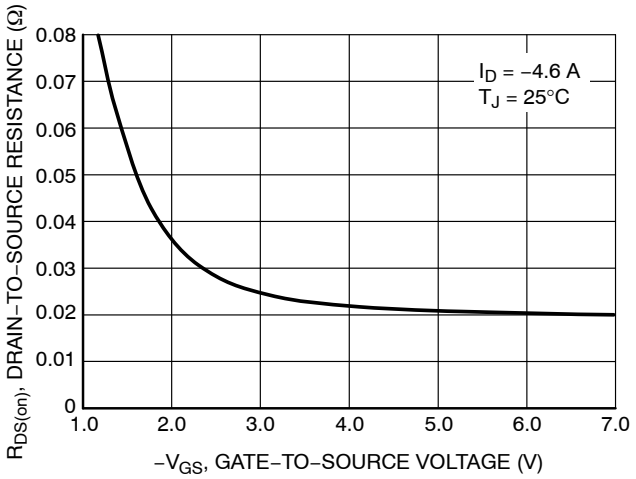


Figure 3. On−Resistance vs. Gate Voltage

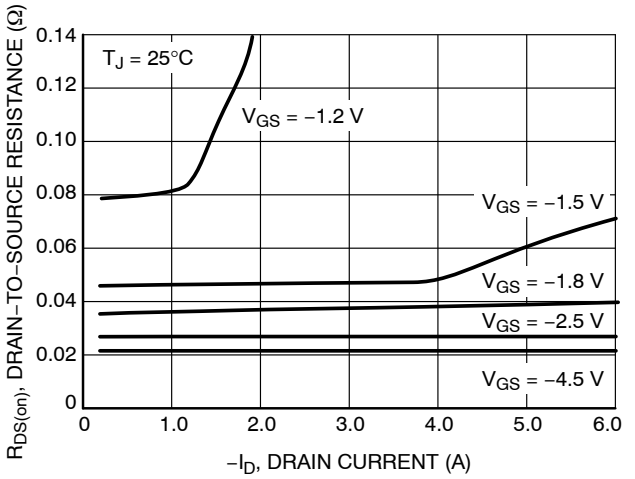


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

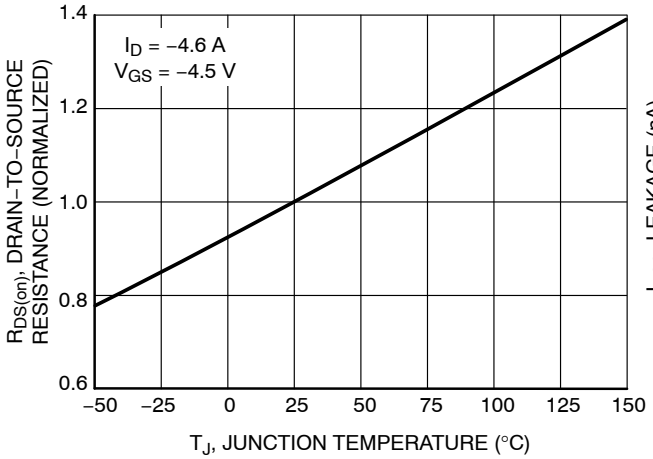


Figure 5. On−Resistance Variation with Temperature

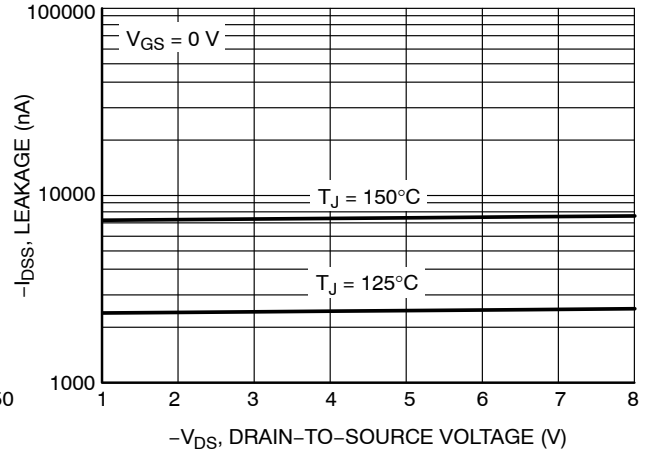


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

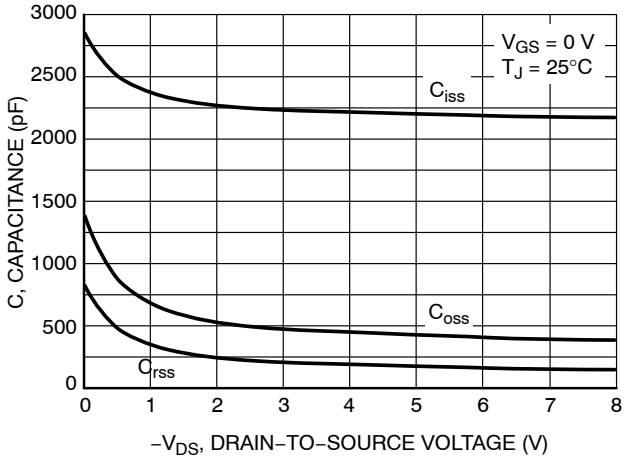


Figure 7. Capacitance Variation

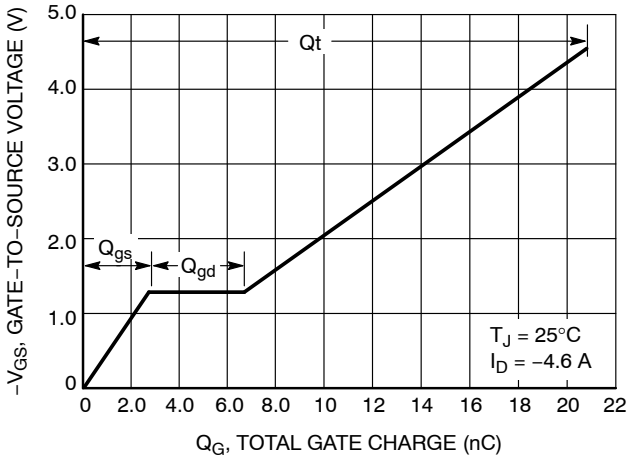


Figure 8. Gate−to−Source Voltage vs. Total Charge

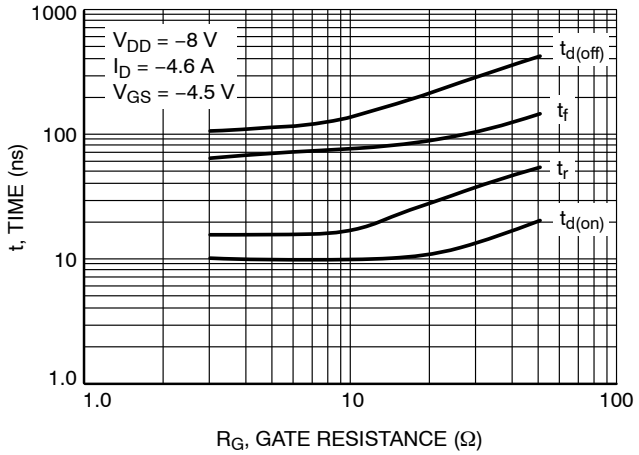


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

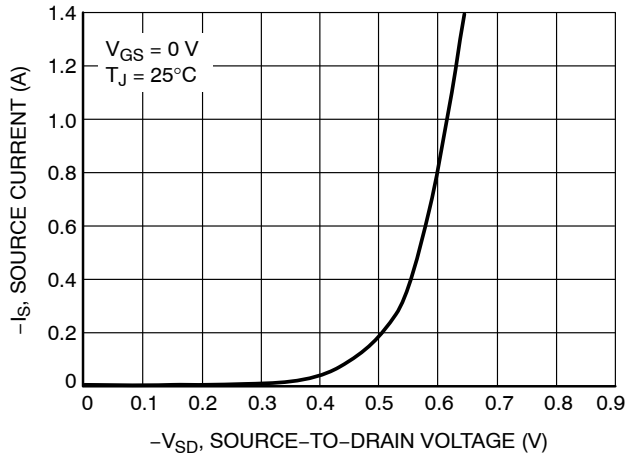
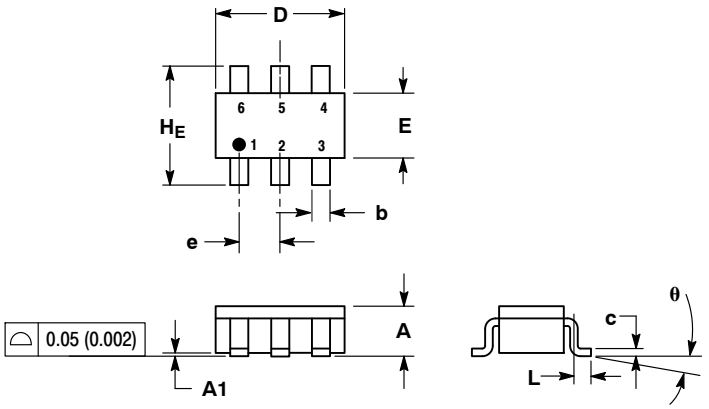


Figure 10. Diode Forward Voltage vs. Current

NTGS1135P

PACKAGE DIMENSIONS

TSOP−6
CASE 318G−02
ISSUE S

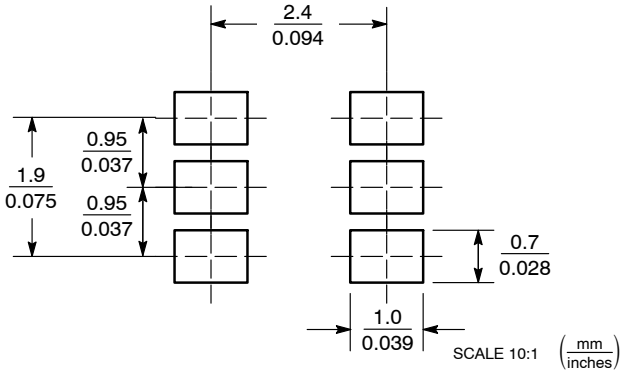


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.38	0.50	0.010	0.014	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	–	10°	0°	–	10°

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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